(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property Organization
International Bureau

(43) International Publication Date
23 June 2011 (23.06.2011)

PCT

(10) International Publication Number
WO 2011/073082 A1

(51) International Patent Classification:
H01L 21/66 (2006.01)

(21) International Application Number:
PCT/EP2010/069300

(22) International Filing Date:
9 December 2010 (09.12.2010)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
09290949.8 15 December 2009 (15.12.2009) EP

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(81) Designated States *(unless otherwise indicated, for every kind of national protection available)*: AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IS, JP, KE, KG, KM, KN, KP, KR, KZ, LA, LC, LK, LR, LS, LT, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PE, PG, PH, PL, PT, RO, RS, RU, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States *(unless otherwise indicated, for every kind of regional protection available)*: ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— *with international search report (Art. 21(3))*

(54) **Title**: METHOD FOR MAKING A SEMICONDUCTOR DEVICE BY LASER IRRADIATION

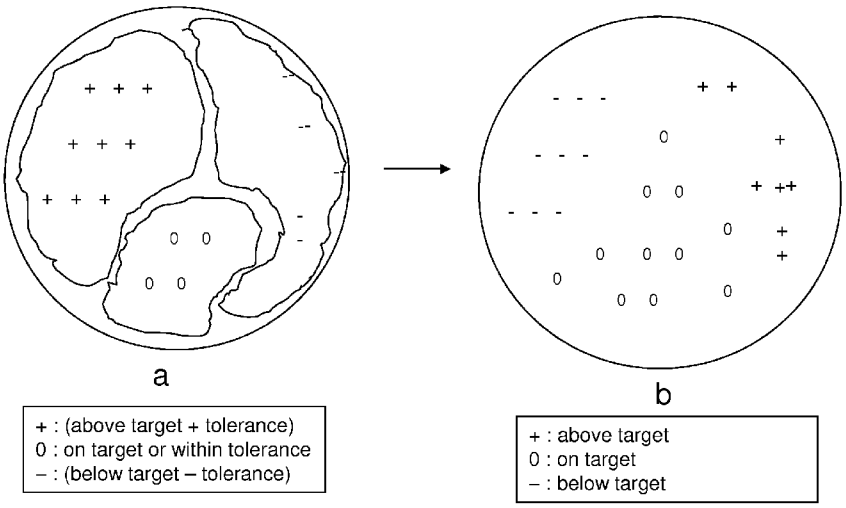


FIG 2

(57) **Abstract**: The present invention is related to a method for making a semiconductor device comprising the steps of : exposing a semiconductor substrate to a process step or sequence of process steps of which at least one process performance parameter is determined in a region of the semiconductor substrate, and irradiating the region with a laser having laser irradiation parameters; characterized in that the irradiation parameters are determined based on the at least one process performance parameter.

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